

L9	14	6 with 8	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/17 14:18
L10	62	6 and @ad<"20000301"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/17 14:42
L11	0	3 and 10	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/17 14:28
L12	1972	3 and @ad<"20000301"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/17 14:42
L13	695	12 and (dram or ram or memory or sram or capacitor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/17 14:43
L14	85	13 and 4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/17 14:45
L15	213	3 with amorph\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/17 14:45
L16	7	15 and 14	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/17 14:51

L19	0	"5688724".pn. and 5	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/17 15:04
L20	47	15 with sapphire	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/17 15:05
L21	0	20 and 7	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/17 15:07
L22	197	"47" and 13	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/17 15:07
L23	3	20 and 13	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/17 15:37
L24	0	23 and n-type	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/17 15:37
L25	0	23 and nmos	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/17 15:37
S13	855147	catalyst	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/14 15:18

S22	14	"6660660"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/16 09:45
S23	39263	"ta.sub.2 o.sub.5" or tao or (tantalum adj1 oxide)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/17 14:16
S24	1635	gate with S23	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/16 09:48
S25	1351	S24 and @ad<"20031109"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/16 15:39
S26	14	"6586797"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/16 13:12
S27	1	("20040097030").PN.	US-PGPUB; USPAT	OR	OFF	2005/11/16 14:53
S28	2	(("20020132422") or ("5933748")). PN.	US-PGPUB; USPAT	OR	OFF	2005/11/16 14:53
S29	39263	"ta.sub.2 o.sub.5" or tao or (tantalum adj1 oxide)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/16 15:39
S30	1635	gate with S29	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/16 15:39
S31	601	S30 and @ad<"20000301"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/17 14:26

S32	313	S31 and (memory or capacitor or dram or ram or sram)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/17 12:44
S33	1	"5688724".pn. and (memory or cell or capacitor or ram or dram or sram)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/17 15:01